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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A9 MPCore™ with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	667MHz
Primary Attributes	Artix™-7 FPGA, 28K Logic Cells
Operating Temperature	-40°C ~ 100°C (TJ)
Package / Case	225-LFBGA, CSPBGA
Supplier Device Package	225-CSPBGA (13x13)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc7z010-1clg225i

Table 1: **Absolute Maximum Ratings(1) *(Cont'd)***

Symbol	Description	Min	Max	Units
V_{IN}(3)(4)(5)	I/O input voltage for HR I/O banks	–0.40	V_{CCO} + 0.55	V
	I/O input voltage (when V_{CCO} = 3.3V) for V_{REF} and differential I/O standards except TMDS_33(6)	–0.40	2.625	V
V_{CCBATT}	Key memory battery backup supply	–0.5	2.0	V
GTP Transceiver (XC7Z015 Only)				
$V_{MGTAVCC}$	Analog supply voltage for the GTP transmitter and receiver circuits	–0.5	1.1	V
$V_{MGTAVTT}$	Analog supply voltage for the GTP transmitter and receiver termination circuits	–0.5	1.32	V
$V_{MGTREFCLK}$	Reference clock absolute input voltage	–0.5	1.32	V
V_{IN}	Receiver (RXP/RXN) and Transmitter (TXP/TXN) absolute input voltage	–0.5	1.26	V
$I_{DCIN-FLOAT}$	DC input current for receiver input pins DC coupled RX termination = floating	–	14	mA
$I_{DCIN-MGTAVTT}$	DC input current for receiver input pins DC coupled RX termination = $V_{MGTAVTT}$	–	12	mA
$I_{DCIN-GND}$	DC input current for receiver input pins DC coupled RX termination = GND	–	6.5	mA
$I_{DCOUT-FLOAT}$	DC output current for transmitter pins DC coupled RX termination = floating	–	14	mA
$I_{DCOUT-MGTAVTT}$	DC output current for transmitter pins DC coupled RX termination = $V_{MGTAVTT}$	–	12	mA
XADC				
V_{CCADC}	XADC supply relative to GNDADC	–0.5	2.0	V
V_{REFP}	XADC reference input relative to GNDADC	–0.5	2.0	V
Temperature				
T_{STG}	Storage temperature (ambient)	–65	150	°C
T_{SOL}	Maximum soldering temperature for Pb/Sn component bodies(7)	–	+220	°C
	Maximum soldering temperature for Pb-free component bodies(7)	–	+260	°C
T_j	Maximum junction temperature(7)	–	+125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. Applies to both MIO supply banks V_{CCO_MIO0} and V_{CCO_MIO1}.
3. The lower absolute voltage specification always applies.
4. For I/O operation, refer to the *7 Series FPGAs SelectIO Resources User Guide* (UG471) or the *Zynq-7000 All Programmable SoC Technical Reference Manual* (UG585).
5. The maximum limit applies to DC signals. For maximum undershoot and overshoot AC specifications, see Table 4.
6. See Table 11 for TMDS_33 specifications.
7. For soldering guidelines and thermal considerations, see the *Zynq-7000 All Programmable SoC Packaging and Pinout Specification* (UG865).

Table 2: **Recommended Operating Conditions(1)(2)**

Symbol	Description	Min	Typ	Max	Units
PS					
V_{CCPINT}	PS internal logic supply voltage	0.95	1.00	1.05	V
V_{CCPAUX}	PS auxiliary supply voltage	1.71	1.80	1.89	V
V_{CCPLL}	PS PLL supply	1.71	1.80	1.89	V
V_{CCO_DDR}	PS DDR I/O supply voltage	1.14	–	1.89	V
V_{CCO_MIO}(3)	PS MIO I/O supply voltage for MIO banks	1.71	–	3.465	V

PS Power-On/Off Power Supply Sequencing

The recommended power-on sequence is V_{CCPINT}, then V_{CCPAUX} and V_{CCPLL} together, then the PS V_{CCO} supplies (V_{CCO_MIO0}, V_{CCO_MIO1}, and V_{CCO_DDR}) to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The PS_POR_B input is required to be asserted to GND during the power-on sequence until V_{CCPINT}, V_{CCPAUX} and V_{CCO_MIO0} have reached minimum operating levels to ensure PS eFUSE integrity. For additional information about PS_POR_B timing requirements refer to Resets.

The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCPAUX}, V_{CCPLL}, and the PS V_{CCO} supplies (V_{CCO_MIO0}, V_{CCO_MIO1}, and V_{CCO_DDR}) have the same recommended voltage levels, then they can be powered by the same supply and ramped simultaneously. Xilinx recommends powering V_{CCPLL} with the same supply as V_{CCPAUX}, with an optional ferrite bead filter. Before V_{CCPINT} reaches 0.80V at least one of the four following conditions is required during the power-off stage: the PS_POR_B input is asserted to GND, the reference clock to the PS_CLK input is disabled, V_{CCPAUX} is lower than 0.70V, or V_{CCO_MIO0} is lower than 0.90V. The condition must be held until V_{CCPINT} reaches 0.40V to ensure PS eFUSE integrity.

For V_{CCO_MIO0} and V_{CCO_MIO1} voltages of 3.3V:

- The voltage difference between V_{CCO_MIO0} /V_{CCO_MIO1} and V_{CCPAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

PL Power-On/Off Power Supply Sequencing

The recommended power-on sequence for the PL is V_{CCINT}, V_{CCBRAM}, V_{CCAUX}, and V_{CCO} to achieve minimum current draw and ensure that the I/Os are 3-stated at power-on. The recommended power-off sequence is the reverse of the power-on sequence. If V_{CCINT} and V_{CCBRAM} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously. If V_{CCAUX} and V_{CCO} have the same recommended voltage levels then both can be powered by the same supply and ramped simultaneously.

For V_{CCO} voltages of 3.3V in HR I/O banks and configuration bank 0:

- The voltage difference between V_{CCO} and V_{CCAUX} must not exceed 2.625V for longer than $T_{VCCO2VCCAUX}$ for each power-on/off cycle to maintain device reliability levels.
- The $T_{VCCO2VCCAUX}$ time can be allocated in any percentage between the power-on and power-off ramps.

GTP Transceivers (XC7Z015 Only)

The recommended power-on sequence to achieve minimum current draw for the GTP transceivers (XC7Z015 only) is V_{CCINT}, $V_{MGTAVCC}$, $V_{MGTAVTT}$ OR $V_{MGTAVCC}$, V_{CCINT}, $V_{MGTAVTT}$. Both $V_{MGTAVCC}$ and V_{CCINT} can be ramped simultaneously. The recommended power-off sequence is the reverse of the power-on sequence to achieve minimum current draw.

If these recommended sequences are not met, current drawn from $V_{MGTAVTT}$ can be higher than specifications during power-up and power-down.

- When $V_{MGTAVTT}$ is powered before $V_{MGTAVCC}$ and $V_{MGTAVTT} - V_{MGTAVCC} > 150$ mV and $V_{MGTAVCC} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 460 mA per transceiver during $V_{MGTAVCC}$ ramp up. The duration of the current draw can be up to 0.3 x $T_{MGTAVCC}$ (ramp time from GND to 90% of $V_{MGTAVCC}$). The reverse is true for power-down.
- When $V_{MGTAVTT}$ is powered before V_{CCINT} and $V_{MGTAVTT} - V_{CCINT} > 150$ mV and $V_{CCINT} < 0.7$V, the $V_{MGTAVTT}$ current draw can increase by 50 mA per transceiver during V_{CCINT} ramp up. The duration of the current draw can be up to 0.3 x T_{VCCINT} (ramp time from GND to 90% of V_{CCINT}). The reverse is true for power-down.

There is no recommended sequence for supplies not shown.

PS—PL Power Sequencing

The PS and PL power supplies are fully independent. PS power supplies (V_{CCPINT}, V_{CCPAUX}, V_{CCPLL}, V_{CCO_DDR}, V_{CCO_MIO0}, and V_{CCO_MIO1}) can be powered before or after any PL power supplies. The PS and PL power regions are isolated to prevent damage.

Power Supply Requirements

Table 6 shows the minimum current, in addition to I_{CCQ}, that is required by Zynq-7000 devices for proper power-on and configuration. If the current minimums shown in Table 5 and Table 6 are met, the device powers on after all four PL supplies have passed through their power-on reset threshold voltages. The Zynq-7000 device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate current drain on these supplies.

Table 6: **Power-On Current for Zynq-7000 Devices**

Device	$I_{CCPINTMIN}$	$I_{CCPAUXMIN}$	$I_{CCDDRMIN}$	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	$I_{CCBRAMMIN}$	Units
XC7Z007S	$I_{CCPINTQ}$ +70	$I_{CCPAUXQ}$ +40	I_{CCDDRQ} + 100 mA per bank	I_{CCINTQ} +40	I_{CCAUXQ} +60	I_{CCOQ} + 90 mA per bank	$I_{CCBRAMQ}$ +40	mA
XC7Z012S	$I_{CCPINTQ}$ +70	$I_{CCPAUXQ}$ +40	I_{CCDDRQ} + 100 mA per bank	I_{CCINTQ} +130	I_{CCAUXQ} +60	I_{CCOQ} + 90 mA per bank	$I_{CCBRAMQ}$ +40	mA
XC7Z014S	$I_{CCPINTQ}$ +70	$I_{CCPAUXQ}$ +40	I_{CCDDRQ} + 100 mA per bank	I_{CCINTQ} +70	I_{CCAUXQ} +60	I_{CCOQ} + 90 mA per bank	$I_{CCBRAMQ}$ +40	mA
XC7Z010 XA7Z010	$I_{CCPINTQ}$ +70	$I_{CCPAUXQ}$ +40	I_{CCDDRQ} + 100 mA per bank	I_{CCINTQ} +40	I_{CCAUXQ} +60	I_{CCOQ} + 90 mA per bank	$I_{CCBRAMQ}$ +40	mA
XC7Z015	$I_{CCPINTQ}$ +70	$I_{CCPAUXQ}$ +40	I_{CCDDRQ} + 100 mA per bank	I_{CCINTQ} +130	I_{CCAUXQ} +60	I_{CCOQ} + 90 mA per bank	$I_{CCBRAMQ}$ +40	mA
XC7Z020 XA7Z020 XQ7Z020	$I_{CCPINTQ}$ +70	$I_{CCPAUXQ}$ +40	I_{CCDDRQ} + 100 mA per bank	I_{CCINTQ} +70	I_{CCAUXQ} +60	I_{CCOQ} + 90 mA per bank	$I_{CCBRAMQ}$ +40	mA

Table 7: **Power Supply Ramp Time**

Symbol	Description	Conditions	Min	Max	Units
$T_{VCCPINT}$	Ramp time from GND to 90% of V_{CCPINT}		0.2	50	ms
$T_{VCCPAUX}$	Ramp time from GND to 90% of V_{CCPAUX}		0.2	50	ms
T_{VCCO_DDR}	Ramp time from GND to 90% of V_{CCO_DDR}		0.2	50	ms
T_{VCCO_MIO}	Ramp time from GND to 90% of V_{CCO_MIO}		0.2	50	ms
T_{VCCINT}	Ramp time from GND to 90% of V_{CCINT}		0.2	50	ms
T_{VCCO}	Ramp time from GND to 90% of V_{CCO}		0.2	50	ms
T_{VCCAUX}	Ramp time from GND to 90% of V_{CCAUX}		0.2	50	ms
$T_{VCCBRAM}$	Ramp time from GND to 90% of V_{CCBRAM}		0.2	50	ms
$T_{VCCO2VCCAUX}$	Allowed time per power cycle for $V_{CCO} - V_{CCAUX} > 2.625V$ and $V_{CCO\_MIO} - V_{CCPAUX} > 2.625V$	$T_j = 125°C$(1)	–	300	ms
		$T_j = 100°C$(1)	–	500	
		$T_j = 85°C$(1)	–	800	
$T_{MGTAVCC}$	Ramp time from GND to 90% of $V_{MGTAVCC}$		0.2	50	ms
$T_{MGTAVTT}$	Ramp time from GND to 90% of $V_{MGTAVTT}$		0.2	50	ms

Notes:

1. Based on 240,000 power cycles with nominal V_{CCO} of 3.3V or 36,500 power cycles with worst case V_{CCO} of 3.465V.

PL I/O Levels

Table 10: **SelectIO DC Input and Output Levels(1)(2)**

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.00	–8.00
HSTL_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSTL_II_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	16.00	–16.00
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.10	–0.10
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 3	Note 3
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	25% V_{CCO}	75% V_{CCO}	Note 4	Note 4
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS25	–0.300	0.7	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS33	–0.300	0.8	2.000	3.450	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVTTL	–0.300	0.8	2.000	3.450	0.400	2.400	Note 5	Note 5
MOBILE_DDR	–0.300	20% V_{CCO}	80% V_{CCO}	V_{CCO} + 0.300	10% V_{CCO}	90% V_{CCO}	0.10	–0.10
PCI33_3	–0.400	30% V_{CCO}	50% V_{CCO}	V_{CCO} + 0.500	10% V_{CCO}	90% V_{CCO}	1.50	–0.50
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.00	–13.00
SSTL135_R	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.90	–8.90
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.00	–13.00
SSTL15_R	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.90	–8.90
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.00	–8.00
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.40	–13.40

Notes:

1. Tested according to relevant specifications.
2. 3.3V and 2.5V standards are only supported in HR I/O banks.
3. Supported drive strengths of 4, 8, or 12 mA in HR I/O banks.
4. Supported drive strengths of 4, 8, 12, or 16 mA in HR I/O banks.
5. Supported drive strengths of 4, 8, 12, 16, or 24 mA in HR I/O banks.
6. For detailed interface specific DC voltage levels, see the *7 Series FPGAs SelectIO Resources User Guide* (UG471).

Table 11: **Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}(1)			V_{ID}(2)			V_{OCM}(3)			V_{OD}(4)		
	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max	V, Min	V, Typ	V, Max
BLVDS_25	0.300	1.200	1.425	0.100	–	–	–	1.250	–	Note 5		
MINI_LVDS_25	0.300	1.200	V_{CCAUX}	0.200	0.400	0.600	1.000	1.200	1.400	0.300	0.450	0.600
PPDS_25	0.200	0.900	V_{CCAUX}	0.100	0.250	0.400	0.500	0.950	1.400	0.100	0.250	0.400
RSDS_25	0.300	0.900	1.500	0.100	0.350	0.600	1.000	1.200	1.400	0.100	0.350	0.600
TMDS_33	2.700	2.965	3.230	0.150	0.675	1.200	V_{CCO}–0.405	V_{CCO}–0.300	V_{CCO}–0.190	0.400	0.600	0.800

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q–$\overline{Q}$).
3. V_{OCM} is the output common mode voltage.
4. V_{OD} is the output differential voltage (Q–$\overline{Q}$).
5. V_{OD} for BLVDS will vary significantly depending on topology and loading.
6. LVDS_25 is specified in Table 13.

Table 12: **Complementary Differential SelectIO DC Input and Output Levels**

I/O Standard	V_{ICM}[1]			V_{ID}[2]		V_{OL}[3]	V_{OH}[4]	I_{OL}	I_{OH}
	V, Min	V,Typ	V, Max	V,Min	V, Max	V, Max	V, Min	mA, Max	mA, Min
DIFF_HSTL_I	0.300	0.750	1.125	0.100	–	0.400	V_{CCO}–0.400	8.00	–8.00
DIFF_HSTL_I_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO}–0.400	8.00	–8.00
DIFF_HSTL_II	0.300	0.750	1.125	0.100	–	0.400	V_{CCO}–0.400	16.00	–16.00
DIFF_HSTL_II_18	0.300	0.900	1.425	0.100	–	0.400	V_{CCO}–0.400	16.00	–16.00
DIFF_HSUL_12	0.300	0.600	0.850	0.100	–	20% V_{CCO}	80% V_{CCO}	0.100	–0.100
DIFF_MOBILE_DDR	0.300	0.900	1.425	0.100	–	10% V_{CCO}	90% V_{CCO}	0.100	–0.100
DIFF_SSTL135	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	13.0	–13.0
DIFF_SSTL135_R	0.300	0.675	1.000	0.100	–	(V_{CCO}/2) – 0.150	(V_{CCO}/2) + 0.150	8.9	–8.9
DIFF_SSTL15	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	13.0	–13.0
DIFF_SSTL15_R	0.300	0.750	1.125	0.100	–	(V_{CCO}/2) – 0.175	(V_{CCO}/2) + 0.175	8.9	–8.9
DIFF_SSTL18_I	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.470	(V_{CCO}/2) + 0.470	8.00	–8.00
DIFF_SSTL18_II	0.300	0.900	1.425	0.100	–	(V_{CCO}/2) – 0.600	(V_{CCO}/2) + 0.600	13.4	–13.4

Notes:

1. V_{ICM} is the input common mode voltage.
2. V_{ID} is the input differential voltage (Q–$\overline{Q}$).
3. V_{OL} is the single-ended low-output voltage.
4. V_{OH} is the single-ended high-output voltage.

LVDS DC Specifications (LVDS_25)

Table 13: **LVDS_25 DC Specifications**[1]

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply voltage		2.375	2.5	2.625	V
V_{OH}	Output High voltage for Q and $\overline{Q}$	R_T = 100Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low voltage for Q and $\overline{Q}$	R_T = 100Ω across Q and $\overline{Q}$ signals	0.700	–	–	V
V_{ODIFF}	Differential output voltage: (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output common-mode voltage	R_T = 100Ω across Q and $\overline{Q}$ signals	1.00	1.25	1.425	V
V_{IDIFF}	Differential input voltage: (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input common-mode voltage		0.3	1.2	1.500	V

Notes:

1. Differential inputs for LVDS_25 can be placed in banks with V_{CCO} levels that are different from the required level for outputs. Consult the *7 Series FPGAs SelectIO Resources User Guide* (UG471) for more information.

To select the -1LI (PL 0.95V) speed specifications in the Vivado tools, select the **Zynq-7000** sub-family and then select the part name that is the device name followed by an *i* followed by the package name followed by the speed grade. For example, select the **xc7z020iclg484-1L** part name for the XC7Z020 device in the CLG484 package and -1LI (PL 0.95V) speed grade. The -1LI (PL 0.95V) speed specifications are not supported in the ISE tools.

A similar part naming convention applies to the speed specifications selection in the ISE tools for supported devices. See Table 16 for the subset of the Zynq-7000 devices supported in the ISE tools.

PS Performance Characteristics

For further design requirement details, refer to the *Zynq-7000 All Programmable SoC Technical Reference Manual* (UG585).

Table 17: **CPU Clock Domains Performance**

Symbol	Clock Ratio	Description	Speed Grade				Units
			-3	-2	-1C/-1I/-1LI	-1Q	
$F_{CPU\_6X4X\_621\_MAX}$(1)	6:2:1	Maximum CPU clock frequency	866	766	667	667	MHz
$F_{CPU\_3X2X\_621\_MAX}$		Maximum CPU_3X clock frequency	433	383	333	333	MHz
$F_{CPU\_2X\_621\_MAX}$		Maximum CPU_2X clock frequency	288	255	222	222	MHz
$F_{CPU\_1X\_621\_MAX}$		Maximum CPU_1X clock frequency	144	127	111	111	MHz
$F_{CPU\_6X4X\_421\_MAX}$(1)	4:2:1	Maximum CPU clock frequency	710	600	533	533	MHz
$F_{CPU\_3X2X\_421\_MAX}$		Maximum CPU_3X clock frequency	355	300	267	267	MHz
$F_{CPU\_2X\_421\_MAX}$		Maximum CPU_2X clock frequency	355	300	267	267	MHz
$F_{CPU\_1X\_421\_MAX}$		Maximum CPU_1X clock frequency	178	150	133	133	MHz

Notes:

1. The maximum frequency during BootROM execution is 500 MHz across all speed specifications.

Table 18: **PS DDR Clock Domains Performance**(1)

Symbol	Description	Speed Grade				Units
		-3	-2	-1C/-1I/-1LI	-1Q	
F_{DDR3_MAX}	Maximum DDR3 interface performance	1066	1066	1066	1066	Mb/s
F_{DDR3L_MAX}	Maximum DDR3L interface performance	1066	1066	1066	1066	Mb/s
F_{DDR2_MAX}	Maximum DDR2 interface performance	800	800	800	800	Mb/s
F_{LPDDR2_MAX}	Maximum LPDDR2 interface performance	800	800	800	800	Mb/s
F_{DDRCLK_2XMAX}	Maximum DDR_2X clock frequency	444	408	355	355	MHz

Notes:

1. All performance numbers apply to both internal and external V_{REF} configurations.

Table 19: **PS-PL Interface Performance**

Symbol	Description	Min	Max	Units
$F_{EMIOGEMCLK}$	EMIO gigabit Ethernet controller maximum frequency	–	125	MHz
$F_{EMIOSDCLK}$	EMIO SD controller maximum frequency	–	25	MHz
$F_{EMIOSPICLK}$	EMIO SPI controller maximum frequency	–	25	MHz
$F_{EMIOJTAGCLK}$	EMIO JTAG controller maximum frequency	–	20	MHz
$F_{EMIOTRACECLK}$	EMIO trace controller maximum frequency	–	125	MHz
F_{FTMCLK}	Fabric trace monitor maximum frequency	–	125	MHz
$F_{EMIODMACLK}$	DMA maximum frequency	–	100	MHz
F_{AXI_MAX}	Maximum AXI interface performance	–	250	MHz

Table 26: **DDR3 Interface Switching Characteristics (800 Mb/s)(1)**

Symbol	Description	Min	Max	Units
$T_{DQVALID}$(2)	Input data valid window	500	–	ps
T_{DQDS}(3)	Output DQ to DQS skew	232	–	ps
T_{DQDH}(4)	Output DQS to DQ skew	401	–	ps
T_{DQSS}	Output clock to DQS skew	–0.10	0.06	T_{CK}
T_{CACK}(5)	Command/address output setup time with respect to CLK	722	–	ps
T_{CKCA}(6)	Command/address output hold time with respect to CLK	882	–	ps

Notes:

1. Recommended V_{CCO_DDR} = 1.5V ±5%.
2. Measurement is taken from V_{REF} to V_{REF}.
3. Measurement is taken from either the rising edge of DQ that crosses V_{IH}(AC) or the falling edge of DQ that crosses V_{IL}(AC) to V_{REF} of DQS.
4. Measurement is taken from either the rising edge of DQ that crosses V_{IL}(DC) or the falling edge of DQ that crosses V_{IH}(DC) to V_{REF} of DQS.
5. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IH}(AC) or the falling edge of CMD/ADDR that crosses V_{IL}(AC) to V_{REF} of CLK.
6. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IL}(DC) or the falling edge of CMD/ADDR that crosses V_{IH}(DC) to V_{REF} of CLK.

Table 27: **DDR3L Interface Switching Characteristics (1066 Mb/s)(1)**

Symbol	Description	Min	Max	Units
$T_{DQVALID}$(2)	Input data valid window	450	–	ps
T_{DQDS}(3)	Output DQ to DQS skew	189	–	ps
T_{DQDH}(4)	Output DQS to DQ skew	267	–	ps
T_{DQSS}	Output clock to DQS skew	–0.13	0.04	T_{CK}
T_{CACK}(5)	Command/address output setup time with respect to CLK	410	–	ps
T_{CKCA}(6)	Command/address output hold time with respect to CLK	629	–	ps

Notes:

1. Recommended V_{CCO_DDR} = 1.35V ±5%.
2. Measurement is taken from V_{REF} to V_{REF}.
3. Measurement is taken from either the rising edge of DQ that crosses V_{IH}(AC) or the falling edge of DQ that crosses V_{IL}(AC) to V_{REF} of DQS.
4. Measurement is taken from either the rising edge of DQ that crosses V_{IL}(DC) or the falling edge of DQ that crosses V_{IH}(DC) to V_{REF} of DQS.
5. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IH}(AC) or the falling edge of CMD/ADDR that crosses V_{IL}(AC) to V_{REF} of CLK.
6. Measurement is taken from either the rising edge of CMD/ADDR that crosses V_{IL}(DC) or the falling edge of CMD/ADDR that crosses V_{IH}(DC) to V_{REF} of CLK.

Table 28: **DDR3L Interface Switching Characteristics (800 Mb/s)(1)**

Symbol	Description	Min	Max	Units
$T_{DQVALID}$(2)	Input data valid window	500	–	ps
T_{DQDS}(3)	Output DQ to DQS skew	321	–	ps
T_{DQDH}(4)	Output DQS to DQ skew	380	–	ps
T_{DQSS}	Output clock to DQS skew	–0.12	0.04	T_{CK}
T_{CACK}(5)	Command/address output setup time with respect to CLK	636	–	ps

Static Memory Controller

Table 33: **SMC Interface Delay Characteristics(1)(2)**

Symbol	Description	Min	Max	Units
$T_{NANDDOUT}$	NAND_IO output delay from last register to pad	4.12	6.45	ns
$T_{NANDALE}$	NAND_ALE output delay from last register to pad	5.08	6.33	ns
$T_{NANDCLE}$	NAND_CLE output delay from last register to pad	4.87	6.40	ns
T_{NANDWE}	NAND_WE_B output delay from last register to pad	4.69	5.89	ns
T_{NANDRE}	NAND_RE_B output delay from last register to pad	5.12	6.44	ns
T_{NANDCE}	NAND_CE_B output delay from last register to pad	4.68	5.89	ns
$T_{NANDDIN}$	NAND_IO setup time and input delay from pad to first register	1.48	3.09	ns
$T_{NANDBUSY}$	NAND_BUSY setup time and input delay from pad to first register	2.48	3.33	ns
T_{SRAMA}	SRAM_A output delay from last register to pad	3.94	5.73	ns
$T_{SRAMDOUT}$	SRAM_DQ output delay from last register to pad	4.66	6.45	ns
T_{SRAMCE}	SRAM_CE output delay from last register to pad	4.57	5.95	ns
T_{SRAMOE}	SRAM_OE_B output delay from last register to pad	4.79	6.13	ns
$T_{SRAMBLS}$	SRAM_BLS_B output delay from last register to pad	5.25	6.74	ns
T_{SRAMWE}	SRAM_WE_B output delay from last register to pad	5.12	6.48	ns
$T_{SRAMDIN}$	SRAM_DQ setup time and input delay from pad to first register	1.93	3.05	ns
$T_{SRAMWAIT}$	SRAM_WAIT setup time and input delay from pad to first register	2.26	3.15	ns
$F_{SMC\_REF\_CLK}$	SMC reference clock frequency	–	100	MHz

Notes:

1. All parameters do not include the package flight time and register controlled delays.
2. Refer to the ARM® PrimeCell® Static Memory Controller (PL350 series) Technical Reference Manual for more SMC timing details.

I2C Interfaces

Table 39: **I2C Fast Mode Interface Switching Characteristics(1)**

Symbol	Description	Min	Typ	Max	Units
$T_{DCI2CFCLK}$	I2C{0,1}SCL duty cycle	–	50	–	%
$T_{I2CFCKO}$	I2C{0,1}SDAO clock to out delay	–	–	900	ns
$T_{I2CFDCK}$	I2C{0,1}SDAI setup time	100	–	–	ns
$F_{I2CFCLK}$	I2C{0,1}SCL clock frequency	–	–	400	KHz

Notes:

1. Test conditions: LVCMOS33, slow slew rate, 8 mA drive strength, 15 pF loads.

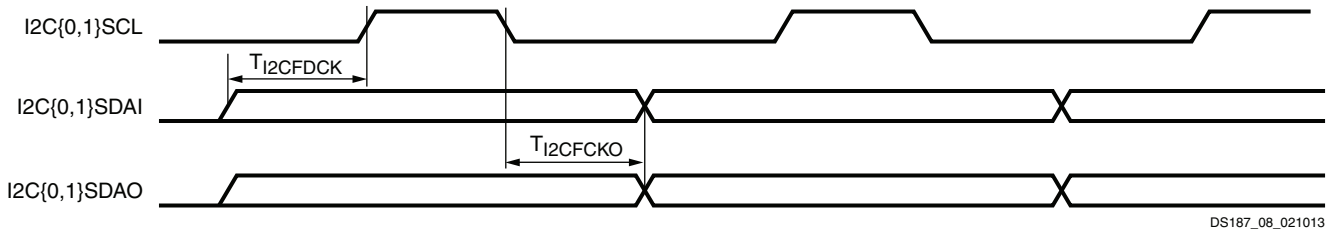

Figure 10: **I2C Fast Mode Interface Timing Diagram**

Table 40: **I2C Standard Mode Interface Switching Characteristics(1)**

Symbol	Description	Min	Typ	Max	Units
$T_{DCI2CSCLK}$	I2C{0,1}SCL duty cycle	–	50	–	%
$T_{I2CSCKO}$	I2C{0,1}SDAO clock to out delay	–	–	3450	ns
$T_{I2CSDCK}$	I2C{0,1}SDAI setup time	250	–	–	ns
$F_{I2CSCLK}$	I2C{0,1}SCL clock frequency	–	–	100	KHz

Notes:

1. Test conditions: LVCMOS33, slow slew rate, 8 mA drive strength, 15 pF loads.

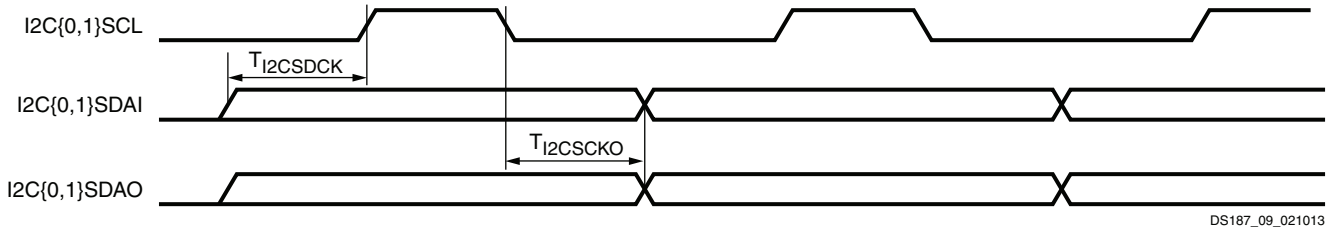

Figure 11: **I2C Standard Mode Interface Timing Diagram**

Table 52: **IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-2	-1C/-1I/-1LI	-1Q	-3	-2	-1C/-1I/-1LI	-1Q	-3	-2	-1C/-1I/-1LI	-1Q	
HSTL_I_18_S	0.67	0.75	0.82	0.88	1.29	1.41	1.67	1.67	1.31	1.44	1.68	1.68	ns
HSTL_II_18_S	0.66	0.75	0.81	0.88	1.41	1.54	1.79	1.79	1.43	1.57	1.80	1.80	ns
DIFF_HSTL_I_S	0.68	0.76	0.83	0.86	1.59	1.71	1.96	1.96	1.60	1.74	1.98	1.98	ns
DIFF_HSTL_II_S	0.68	0.76	0.83	0.86	1.51	1.63	1.88	1.88	1.52	1.66	1.90	1.90	ns
DIFF_HSTL_I_18_S	0.71	0.79	0.86	0.86	1.38	1.51	1.76	1.76	1.40	1.54	1.77	1.77	ns
DIFF_HSTL_II_18_S	0.70	0.78	0.85	0.88	1.46	1.58	1.84	1.84	1.48	1.61	1.85	1.85	ns
HSTL_I_F	0.67	0.75	0.82	0.86	1.10	1.22	1.48	1.49	1.12	1.25	1.49	1.51	ns
HSTL_II_F	0.65	0.73	0.80	0.86	1.12	1.24	1.49	1.49	1.13	1.27	1.51	1.51	ns
HSTL_I_18_F	0.67	0.75	0.82	0.88	1.13	1.26	1.51	1.54	1.15	1.29	1.52	1.56	ns
HSTL_II_18_F	0.66	0.75	0.81	0.88	1.12	1.24	1.49	1.51	1.13	1.27	1.51	1.52	ns
DIFF_HSTL_I_F	0.68	0.76	0.83	0.86	1.18	1.30	1.56	1.56	1.20	1.33	1.57	1.57	ns
DIFF_HSTL_II_F	0.68	0.76	0.83	0.86	1.21	1.33	1.59	1.59	1.23	1.36	1.60	1.60	ns
DIFF_HSTL_I_18_F	0.71	0.79	0.86	0.86	1.21	1.33	1.59	1.59	1.23	1.36	1.60	1.60	ns
DIFF_HSTL_II_18_F	0.70	0.78	0.85	0.88	1.21	1.33	1.59	1.59	1.23	1.36	1.60	1.60	ns
LVCMOS33_S4	1.26	1.34	1.41	1.52	3.80	3.93	4.18	4.18	3.82	3.96	4.20	4.20	ns
LVCMOS33_S8	1.26	1.34	1.41	1.52	3.52	3.65	3.90	3.90	3.54	3.68	3.91	3.91	ns
LVCMOS33_S12	1.26	1.34	1.41	1.52	3.09	3.21	3.46	3.46	3.10	3.24	3.48	3.48	ns
LVCMOS33_S16	1.26	1.34	1.41	1.52	3.40	3.52	3.77	3.78	3.42	3.55	3.79	3.79	ns
LVCMOS33_F4	1.26	1.34	1.41	1.52	3.26	3.38	3.64	3.64	3.28	3.41	3.65	3.65	ns
LVCMOS33_F8	1.26	1.34	1.41	1.52	2.74	2.87	3.12	3.12	2.76	2.90	3.13	3.13	ns
LVCMOS33_F12	1.26	1.34	1.41	1.52	2.56	2.68	2.93	2.93	2.57	2.71	2.95	2.95	ns
LVCMOS33_F16	1.26	1.34	1.41	1.52	2.56	2.68	2.93	3.06	2.57	2.71	2.95	3.07	ns
LVCMOS25_S4	1.12	1.20	1.27	1.38	3.13	3.26	3.51	3.51	3.15	3.29	3.52	3.52	ns
LVCMOS25_S8	1.12	1.20	1.27	1.38	2.88	3.01	3.26	3.26	2.90	3.04	3.27	3.27	ns
LVCMOS25_S12	1.12	1.20	1.27	1.38	2.48	2.60	2.85	2.85	2.49	2.63	2.87	2.87	ns
LVCMOS25_S16	1.12	1.20	1.27	1.38	2.82	2.94	3.20	3.20	2.84	2.97	3.21	3.21	ns
LVCMOS25_F4	1.12	1.20	1.27	1.38	2.74	2.87	3.12	3.12	2.76	2.90	3.13	3.13	ns
LVCMOS25_F8	1.12	1.20	1.27	1.38	2.18	2.30	2.56	2.56	2.20	2.33	2.57	2.57	ns
LVCMOS25_F12	1.12	1.20	1.27	1.38	2.16	2.29	2.54	2.54	2.18	2.32	2.55	2.56	ns
LVCMOS25_F16	1.12	1.20	1.27	1.38	2.01	2.13	2.39	2.63	2.03	2.16	2.40	2.65	ns
LVCMOS18_S4	0.74	0.83	0.89	0.97	1.62	1.74	1.99	1.99	1.63	1.77	2.01	2.01	ns
LVCMOS18_S8	0.74	0.83	0.89	0.97	2.18	2.30	2.56	2.56	2.20	2.33	2.57	2.57	ns
LVCMOS18_S12	0.74	0.83	0.89	0.97	2.18	2.30	2.56	2.56	2.20	2.33	2.57	2.57	ns
LVCMOS18_S16	0.74	0.83	0.89	0.97	1.52	1.65	1.90	1.90	1.54	1.68	1.91	1.91	ns
LVCMOS18_S24	0.74	0.83	0.89	0.97	1.60	1.72	1.98	2.40	1.62	1.75	1.99	2.41	ns
LVCMOS18_F4	0.74	0.83	0.89	0.97	1.45	1.57	1.82	1.82	1.46	1.60	1.84	1.84	ns
LVCMOS18_F8	0.74	0.83	0.89	0.97	1.68	1.80	2.06	2.06	1.70	1.83	2.07	2.07	ns
LVCMOS18_F12	0.74	0.83	0.89	0.97	1.68	1.80	2.06	2.06	1.70	1.83	2.07	2.07	ns
LVCMOS18_F16	0.74	0.83	0.89	0.97	1.40	1.52	1.77	1.78	1.42	1.55	1.79	1.79	ns

Table 52: **IOB High Range (HR) Switching Characteristics *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-2	-1C/-1I/-1LI	-1Q	-3	-2	-1C/-1I/-1LI	-1Q	-3	-2	-1C/-1I/-1LI	-1Q	
LVCMOS18_F24	0.74	0.83	0.89	0.97	1.34	1.46	1.71	2.28	1.35	1.49	1.73	2.29	ns
LVCMOS15_S4	0.77	0.86	0.93	0.96	2.05	2.18	2.43	2.43	2.07	2.21	2.45	2.45	ns
LVCMOS15_S8	0.77	0.86	0.93	0.96	2.09	2.21	2.46	2.46	2.10	2.24	2.48	2.48	ns
LVCMOS15_S12	0.77	0.86	0.93	0.96	1.59	1.71	1.96	1.96	1.60	1.74	1.98	1.98	ns
LVCMOS15_S16	0.77	0.86	0.93	0.96	1.59	1.71	1.96	1.96	1.60	1.74	1.98	1.98	ns
LVCMOS15_F4	0.77	0.86	0.93	0.96	1.85	1.97	2.23	2.23	1.87	2.00	2.24	2.24	ns
LVCMOS15_F8	0.77	0.86	0.93	0.96	1.60	1.72	1.98	1.98	1.62	1.75	1.99	1.99	ns
LVCMOS15_F12	0.77	0.86	0.93	0.96	1.35	1.47	1.73	1.73	1.37	1.50	1.74	1.74	ns
LVCMOS15_F16	0.77	0.86	0.93	0.96	1.34	1.46	1.71	2.07	1.35	1.49	1.73	2.09	ns
LVCMOS12_S4	0.87	0.95	1.02	1.19	2.57	2.69	2.95	2.95	2.59	2.72	2.96	2.96	ns
LVCMOS12_S8	0.87	0.95	1.02	1.19	2.09	2.21	2.46	2.46	2.10	2.24	2.48	2.48	ns
LVCMOS12_S12	0.87	0.95	1.02	1.19	1.79	1.91	2.17	2.17	1.81	1.94	2.18	2.18	ns
LVCMOS12_F4	0.87	0.95	1.02	1.19	1.98	2.10	2.35	2.35	1.99	2.13	2.37	2.37	ns
LVCMOS12_F8	0.87	0.95	1.02	1.19	1.54	1.66	1.92	1.92	1.56	1.69	1.93	1.93	ns
LVCMOS12_F12	0.87	0.95	1.02	1.19	1.38	1.51	1.76	1.76	1.40	1.54	1.77	1.77	ns
SSTL135_S	0.67	0.75	0.82	0.88	1.35	1.47	1.73	1.73	1.37	1.50	1.74	1.74	ns
SSTL15_S	0.60	0.68	0.75	0.75	1.30	1.43	1.68	1.71	1.32	1.46	1.69	1.73	ns
SSTL18_I_S	0.67	0.75	0.82	0.86	1.67	1.79	2.04	2.04	1.68	1.82	2.06	2.06	ns
SSTL18_II_S	0.67	0.75	0.82	0.88	1.31	1.43	1.68	1.68	1.32	1.46	1.70	1.70	ns
DIFF_SSTL135_S	0.68	0.76	0.83	0.88	1.35	1.47	1.73	1.73	1.37	1.50	1.74	1.74	ns
DIFF_SSTL15_S	0.68	0.76	0.83	0.88	1.30	1.43	1.68	1.71	1.32	1.46	1.69	1.73	ns
DIFF_SSTL18_I_S	0.71	0.79	0.86	0.88	1.68	1.80	2.06	2.06	1.70	1.83	2.07	2.07	ns
DIFF_SSTL18_II_S	0.71	0.79	0.86	0.88	1.38	1.51	1.76	1.76	1.40	1.54	1.77	1.77	ns
SSTL135_F	0.67	0.75	0.82	0.88	1.12	1.24	1.49	1.49	1.13	1.27	1.51	1.51	ns
SSTL15_F	0.60	0.68	0.75	0.75	1.07	1.19	1.45	1.45	1.09	1.22	1.46	1.46	ns
SSTL18_I_F	0.67	0.75	0.82	0.86	1.12	1.24	1.49	1.53	1.13	1.27	1.51	1.54	ns
SSTL18_II_F	0.67	0.75	0.82	0.88	1.12	1.24	1.49	1.51	1.13	1.27	1.51	1.52	ns
DIFF_SSTL135_F	0.68	0.76	0.83	0.88	1.12	1.24	1.49	1.49	1.13	1.27	1.51	1.51	ns
DIFF_SSTL15_F	0.68	0.76	0.83	0.88	1.07	1.19	1.45	1.45	1.09	1.22	1.46	1.46	ns
DIFF_SSTL18_I_F	0.71	0.79	0.86	0.88	1.23	1.35	1.60	1.60	1.24	1.38	1.62	1.62	ns
DIFF_SSTL18_II_F	0.71	0.79	0.86	0.88	1.21	1.33	1.59	1.59	1.23	1.36	1.60	1.60	ns

Table 53 specifies the values of T_{IOTPHZ} and $T_{IOIBUFDISABLE}$. T_{IOTPHZ} is described as the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is enabled (i.e., a high impedance state). $T_{IOIBUFDISABLE}$ is described as the IOB delay from IBUFDISABLE to O output. In HR I/O banks, the internal IN_TERM termination turn-off time is always faster than T_{IOTPHZ} when the INTERMDISABLE pin is used.

Table 53: **IOB 3-state Output Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1C/-1I/-1LI	-1Q	
T_{IOTPHZ}	T input to pad high-impedance	2.06	2.19	2.37	2.37	ns
$T_{IOIBUFDISABLE}$	IBUF turn-on time from IBUFDISABLE to O output	2.11	2.30	2.60	2.60	ns

I/O Standard Adjustment Measurement Methodology

Input Delay Measurements

Table 54 shows the test setup parameters used for measuring input delay.

Table 54: **Input Delay Measurement Methodology**

Description	I/O Standard Attribute	V_L (1)(2)	V_H (1)(2)	V_{MEAS} (1)(4)(6)	V_{REF} (1)(3)(5)
LVCMOS, 1.2V	LVCMOS12	0.1	1.1	0.6	–
LVCMOS, 1.5V	LVCMOS15	0.1	1.4	0.75	–
LVCMOS, 1.8V	LVCMOS18	0.1	1.7	0.9	–
LVCMOS, 2.5V	LVCMOS25	0.1	2.4	1.25	–
LVCMOS, 3.3V	LVCMOS33	0.1	3.2	1.65	–
LVTTL, 3.3V	LVTTL	0.1	3.2	1.65	–
MOBILE_DDR, 1.8V	MOBILE_DDR	0.1	1.7	0.9	–
PCI33, 3.3V	PCI33_3	0.1	3.2	1.65	–
HSTL (High-Speed Transceiver Logic), Class I, 1.2V	HSTL_I_12	V_{REF} – 0.5	V_{REF} + 0.5	V_{REF}	0.60
HSTL, Class I & II, 1.5V	HSTL_I, HSTL_II	V_{REF} – 0.65	V_{REF} + 0.65	V_{REF}	0.75
HSTL, Class I & II, 1.8V	HSTL_I_18, HSTL_II_18	V_{REF} – 0.8	V_{REF} + 0.8	V_{REF}	0.90
HSUL (High-Speed Unterminated Logic), 1.2V	HSUL_12	V_{REF} – 0.5	V_{REF} + 0.5	V_{REF}	0.60
SSTL (Stub Terminated Transceiver Logic), 1.2V	SSTL12	V_{REF} – 0.5	V_{REF} + 0.5	V_{REF}	0.60
SSTL, 1.35V	SSTL135, SSTL135_R	V_{REF} – 0.575	V_{REF} + 0.575	V_{REF}	0.675
SSTL, 1.5V	SSTL15, SSTL15_R	V_{REF} – 0.65	V_{REF} + 0.65	V_{REF}	0.75
SSTL, Class I & II, 1.8V	SSTL18_I, SSTL18_II	V_{REF} – 0.8	V_{REF} + 0.8	V_{REF}	0.90
DIFF_MOBILE_DDR, 1.8V	DIFF_MOBILE_DDR	0.9 – 0.125	0.9 + 0.125	0 (6)	–
DIFF_HSTL, Class I, 1.2V	DIFF_HSTL_I_12	0.6 – 0.125	0.6 + 0.125	0 (6)	–
DIFF_HSTL, Class I & II,1.5V	DIFF_HSTL_I, DIFF_HSTL_II	0.75 – 0.125	0.75 + 0.125	0 (6)	–
DIFF_HSTL, Class I & II, 1.8V	DIFF_HSTL_I_18, DIFF_HSTL_II_18	0.9 – 0.125	0.9 + 0.125	0 (6)	–
DIFF_HSUL, 1.2V	DIFF_HSUL_12	0.6 – 0.125	0.6 + 0.125	0 (6)	–
DIFF_SSTL, 1.2V	DIFF_SSTL12	0.6 – 0.125	0.6 + 0.125	0 (6)	–
DIFF_SSTL135/DIFF_SSTL135_R, 1.35V	DIFF_SSTL135, DIFF_SSTL135_R	0.675 – 0.125	0.675 + 0.125	0 (6)	–
DIFF_SSTL15/DIFF_SSTL15_R, 1.5V	DIFF_SSTL15, DIFF_SSTL15_R	0.75 – 0.125	0.75 + 0.125	0 (6)	–
DIFF_SSTL18_I/DIFF_SSTL18_II, 1.8V	DIFF_SSTL18_I, DIFF_SSTL18_II	0.9 – 0.125	0.9 + 0.125	0 (6)	–
LVDS (Low-Voltage Differential Signaling), 1.8V	LVDS	0.9 – 0.125	0.9 + 0.125	0 (6)	–

Table 54: **Input Delay Measurement Methodology *(Cont'd)***

Description	I/O Standard Attribute	V_L (1)(2)	V_H (1)(2)	V_{MEAS} (1)(4)(6)	V_{REF} (1)(3)(5)
LVDS_25, 2.5V	LVDS_25	1.2 – 0.125	1.2 + 0.125	0(6)	–
BLVDS_25, 2.5V	BLVDS_25	1.25 – 0.125	1.25 + 0.125	0(6)	–
MINI_LVDS_25, 2.5V	MINI_LVDS_25	1.25 – 0.125	1.25 + 0.125	0(6)	–
PPDS_25	PPDS_25	1.25 – 0.125	1.25 + 0.125	0(6)	–
RSDS_25	RSDS_25	1.25 – 0.125	1.25 + 0.125	0(6)	–
TMDS_33	TMDS_33	3 – 0.125	3 + 0.125	0(6)	–

Notes:

1. The input delay measurement methodology parameters for LVDCI are the same for LVCMOS standards of the same voltage. Input delay measurement methodology parameters for HSLVDCI are the same as for HSTL_II standards of the same voltage. Parameters for all other DCI standards are the same for the corresponding non-DCI standards.
2. Input waveform switches between V_L and V_H.
3. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
4. Input voltage level from which measurement starts.
5. This is an input voltage reference that bears no relation to the V_{REF} / V_{MEAS} parameters found in IBIS models and/or noted in Figure 18.
6. The value given is the differential input voltage.

Output Delay Measurements

Output delays are measured with short output traces. Standard termination was used for all testing. The propagation delay of the trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 18 and Figure 19.

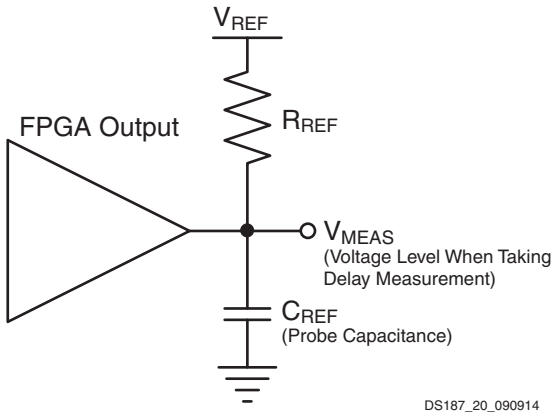

Figure 18: **Single-Ended Test Setup**

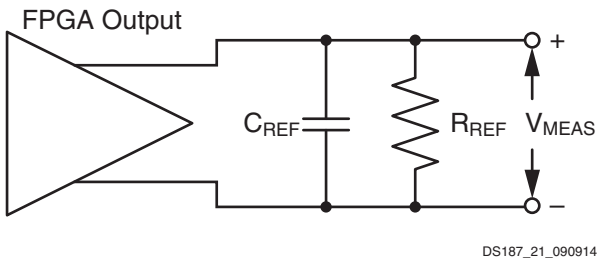

Figure 19: **Differential Test Setup**

Table 57: **OLOGIC Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		-3	-2	-1C/-1I/-1LI	-1Q	
T_{OTCECK}/ T_{OCKTCE}	TCE pin setup/hold with respect to CLK	0.32/0.01	0.34/0.01	0.51/0.01	0.51/0.01	ns
Combinatorial						
T_{ODQ}	D1 to OQ out or T1 to TQ out	0.83	0.96	1.16	1.16	ns
Sequential Delays						
T_{OCKQ}	CLK to OQ/TQ out	0.47	0.49	0.56	0.56	ns
T_{RQ_OLOGIC}	SR pin to OQ/TQ out	0.72	0.80	0.95	0.95	ns
T_{GSRQ_OLOGIC}	Global set/reset to Q outputs	7.60	7.60	10.51	10.51	ns
Set/Reset						
T_{RPW_OLOGIC}	Minimum pulse width, SR inputs	0.64	0.74	0.74	0.74	ns, Min

Input Serializer/Deserializer Switching Characteristics

Table 58: **ISERDES Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1C/-1I/-1LI	-1Q	
Setup/Hold for Control Lines						
$T_{ISCCK\_BITSLIP}$/ $T_{ISCKC\_BITSLIP}$	BITSLIP pin setup/hold with respect to CLKDIV	0.01/0.14	0.02/0.15	0.02/0.17	0.02/0.17	ns
T_{ISCCK_CE} / T_{ISCKC_CE}(2)	CE pin setup/hold with respect to CLK (for CE1)	0.45/–0.01	0.50/–0.01	0.72/–0.01	0.72/–0.01	ns
T_{ISCCK_CE2} / T_{ISCKC_CE2}(2)	CE pin setup/hold with respect to CLKDIV (for CE2)	–0.10/0.33	–0.10/0.36	–0.10/0.40	–0.10/0.40	ns
Setup/Hold for Data Lines						
T_{ISDCK_D} /T_{ISCKD_D}	D pin setup/hold with respect to CLK	–0.02/0.12	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
T_{ISDCK_DDLY}/ T_{ISCKD_DDLY}	DDLY pin setup/hold with respect to CLK (using IDELAY)(1)	–0.02/0.12	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
$T_{ISDCK\_D\_DDR}$/ $T_{ISCKD\_D\_DDR}$	D pin setup/hold with respect to CLK at DDR mode	–0.02/0.12	–0.02/0.14	–0.02/0.17	–0.02/0.17	ns
$T_{ISDCK\_DDLY\_DDR}$/ $T_{ISCKD\_DDLY\_DDR}$	D pin setup/hold with respect to CLK at DDR mode (using IDELAY)(1)	0.12/0.12	0.14/0.14	0.17/0.17	0.17/0.17	ns
Sequential Delays						
T_{ISCKO_Q}	CLKDIV to out at Q pin	0.53	0.54	0.66	0.66	ns
Propagation Delays						
T_{ISDO_DO}	D input to DO output pin	0.11	0.11	0.13	0.13	ns

Notes:

1. Recorded at 0 tap value.
2. T_{ISCCK_CE2} and T_{ISCKC_CE2} are reported as T_{ISCCK_CE}/T_{ISCKC_CE} in the timing report.

Table 63: **CLB Distributed RAM Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		-3	-2	-1C/-1I/-1LI	-1Q	
Setup and Hold Times Before/After Clock CLK						
T_{DS_LRAM}/ T_{DH_LRAM}	A – D inputs to CLK	0.54/0.28	0.60/0.30	0.72/0.35	0.72/0.37	ns, Min
T_{AS_LRAM}/ T_{AH_LRAM}	Address An inputs to clock	0.27/0.55	0.30/0.60	0.37/0.70	0.37/0.71	ns, Min
	Address An inputs through MUXs and/or carry logic to clock	0.69/0.18	0.77/0.21	0.94/0.26	0.94/0.35	ns, Min
T_{WS_LRAM}/ T_{WH_LRAM}	WE input to clock	0.38/0.10	0.43/0.12	0.53/0.17	0.53/0.17	ns, Min
T_{CECK_LRAM}/ T_{CKCE_LRAM}	CE input to CLK	0.39/0.10	0.44/0.11	0.53/0.17	0.53/0.17	ns, Min
Clock CLK						
T_{MPW_LRAM}	Minimum pulse width	1.05	1.13	1.25	1.25	ns, Min
T_{MCP}	Minimum clock period	2.10	2.26	2.50	2.50	ns, Min

Notes:

1. T_{SHCKO} also represents the CLK to XMUX output. Refer to the timing report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 64: **CLB Shift Register Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1C/-1I/-1LI	-1Q	
Sequential Delays						
T_{REG}	Clock to A – D outputs	1.19	1.33	1.61	1.61	ns, Max
T_{REG_MUX}	Clock to AMUX – DMUX output	1.58	1.77	2.15	2.15	ns, Max
T_{REG_M31}	Clock to DMUX output via M31 output	1.12	1.23	1.46	1.46	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{WS_SHFREG}/ T_{WH_SHFREG}	WE input	0.37/0.10	0.41/0.12	0.51/0.17	0.51/0.17	ns, Min
T_{CECK_SHFREG}/ T_{CKCE_SHFREG}	CE input to CLK	0.37/0.10	0.42/0.11	0.52/0.17	0.52/0.17	ns, Min
T_{DS_SHFREG}/ T_{DH_SHFREG}	A – D inputs to CLK	0.33/0.34	0.37/0.37	0.44/0.43	0.44/0.44	ns, Min
Clock CLK						
T_{MPW_SHFREG}	Minimum pulse width	0.77	0.86	0.98	0.98	ns, Min

Table 66: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		-3	-2	-1C/-1I/-1LI	-1Q	
$T_{DSPDCK\_RSTP\_PREG}$/ $T_{DSPCKD\_RSTP\_PREG}$	RSTP input to P register CLK	0.27/0.01	0.30/0.01	0.35/0.01	0.35/0.03	ns
Combinatorial Delays from Input Pins to Output Pins						
$T_{DSPDO\_A\_CARRYOUT\_MULT}$	A input to CARRYOUT output using multiplier	3.79	4.35	5.18	5.18	ns
$T_{DSPDO\_D\_P\_MULT}$	D input to P output using multiplier	3.72	4.26	5.07	5.07	ns
$T_{DSPDO\_A\_P}$	A input to P output not using multiplier	1.53	1.75	2.08	2.08	ns
$T_{DSPDO\_C\_P}$	C input to P output	1.33	1.53	1.82	1.82	ns
Combinatorial Delays from Input Pins to Cascading Output Pins						
$T_{DSPDO\_\{A; B\}\_\{ACOUT; BCOUT\}}$	{A, B} input to {ACOUT, BCOUT} output	0.55	0.63	0.74	0.74	ns
$T_{DSPDO\_\{A, B\}\_CARRYCASCOUT\_MULT}$	{A, B} input to CARRYCASCOUT output using multiplier	4.06	4.65	5.54	5.54	ns
$T_{DSPDO\_D\_CARRYCASCOUT\_MULT}$	D input to CARRYCASCOUT output using multiplier	3.97	4.54	5.40	5.40	ns
$T_{DSPDO\_\{A, B\}\_CARRYCASCOUT}$	{A, B} input to CARRYCASCOUT output not using multiplier	1.77	2.03	2.41	2.41	ns
$T_{DSPDO\_C\_CARRYCASCOUT}$	C input to CARRYCASCOUT output	1.58	1.81	2.15	2.15	ns
Combinatorial Delays from Cascading Input Pins to All Output Pins						
$T_{DSPDO\_ACIN\_P\_MULT}$	ACIN input to P output using multiplier	3.65	4.19	5.00	5.00	ns
$T_{DSPDO\_ACIN\_P}$	ACIN input to P output not using multiplier	1.37	1.57	1.88	1.88	ns
$T_{DSPDO\_ACIN\_ACOUT}$	ACIN input to ACOUT output	0.38	0.44	0.53	0.53	ns
$T_{DSPDO\_ACIN\_CARRYCASCOUT\_MULT}$	ACIN input to CARRYCASCOUT output using multiplier	3.90	4.47	5.33	5.33	ns
$T_{DSPDO\_ACIN\_CARRYCASCOUT}$	ACIN input to CARRYCASCOUT output not using multiplier	1.61	1.85	2.21	2.21	ns
$T_{DSPDO\_PCIN\_P}$	PCIN input to P output	1.11	1.28	1.52	1.52	ns
$T_{DSPDO\_PCIN\_CARRYCASCOUT}$	PCIN input to CARRYCASCOUT output	1.36	1.56	1.85	1.85	ns
Clock to Outs from Output Register Clock to Output Pins						
$T_{DSPCKO\_P\_PREG}$	CLK PREG to P output	0.33	0.37	0.44	0.44	ns
$T_{DSPCKO\_CARRYCASCOUT\_PREG}$	CLK PREG to CARRYCASCOUT output	0.52	0.59	0.69	0.69	ns
Clock to Outs from Pipeline Register Clock to Output Pins						
$T_{DSPCKO\_P\_MREG}$	CLK MREG to P output	1.68	1.93	2.31	2.31	ns
$T_{DSPCKO\_CARRYCASCOUT\_MREG}$	CLK MREG to CARRYCASCOUT output	1.92	2.21	2.64	2.64	ns
$T_{DSPCKO\_P\_ADREG\_MULT}$	CLK ADREG to P output using multiplier	2.72	3.10	3.69	3.69	ns
$T_{DSPCKO\_CARRYCASCOUT\_ADREG\_MULT}$	CLK ADREG to CARRYCASCOUT output using multiplier	2.96	3.38	4.02	4.02	ns

Table 71: **Duty-Cycle Distortion and Clock-Tree Skew**

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1C/-1I/-1LI	-1Q	
T_{DCD_CLK}	Global clock tree duty-cycle distortion(1)	All	0.20	0.20	0.20	0.20	ns
T_{CKSKEW}	Global clock tree skew(2)	XC7Z007S	N/A	0.27	0.27	N/A	ns
		XC7Z012S	N/A	0.39	0.42	N/A	ns
		XC7Z014S	N/A	0.38	0.42	N/A	ns
		XC7Z010	0.27	0.27	0.27	N/A	ns
		XC7Z015	0.33	0.39	0.42	N/A	ns
		XC7Z020	0.33	0.38	0.42	N/A	ns
		XA7Z010	N/A	N/A	0.27	0.27	ns
		XA7Z020	N/A	N/A	0.42	0.42	ns
		XQ7Z020	N/A	0.38	0.42	0.42	ns
T_{DCD_BUFIO}	I/O clock tree duty-cycle distortion	All	0.14	0.14	0.14	0.14	ns
$T_{BUFIOSKEW}$	I/O clock tree skew across one clock region	All	0.03	0.03	0.03	0.03	ns
T_{DCD_BUFR}	Regional clock tree duty-cycle distortion	All	0.18	0.18	0.18	0.18	ns

Notes:

1. These parameters represent the worst-case duty-cycle distortion observable at the pins of the device using LVDS output buffers. For cases where other I/O standards are used, IBIS can be used to calculate any additional duty-cycle distortion that might be caused by asymmetrical rise/fall times.
2. The T_{CKSKEW} value represents the worst-case clock-tree skew observable between sequential I/O elements. Significantly less clock-tree skew exists for I/O registers that are close to each other and fed by the same or adjacent clock-tree branches. Use the Xilinx Timing Analyzer tools to evaluate application specific clock skew.

MMCM Switching Characteristics

Table 72: **MMCM Specification**

Symbol	Description	Speed Grade				Units
		-3	-2	-1C/-1I/-1LI	-1Q	
$MMCM\_F_{INMAX}$	Maximum input clock frequency	800.00	800.00	800.00	800.00	MHz
$MMCM\_F_{INMIN}$	Minimum input clock frequency	10.00	10.00	10.00	10.00	MHz
$MMCM\_F_{INJITTER}$	Maximum input clock period jitter	< 20% of clock input period or 1 ns Max				
$MMCM\_F_{INDUTY}$	Allowable input duty cycle: 10—49 MHz	25	25	25	25	%
	Allowable input duty cycle: 50—199 MHz	30	30	30	30	%
	Allowable input duty cycle: 200—399 MHz	35	35	35	35	%
	Allowable input duty cycle: 400—499 MHz	40	40	40	40	%
	Allowable input duty cycle: >500 MHz	45	45	45	45	%
$MMCM\_F_{MIN\_PSCLK}$	Minimum dynamic phase-shift clock frequency	0.01	0.01	0.01	0.01	MHz
$MMCM\_F_{MAX\_PSCLK}$	Maximum dynamic phase-shift clock frequency	550.00	500.00	450.00	450.00	MHz
$MMCM\_F_{VCOMIN}$	Minimum MMCM VCO frequency	600.00	600.00	600.00	600.00	MHz
$MMCM\_F_{VCOMAX}$	Maximum MMCM VCO frequency	1600.00	1440.00	1200.00	1200.00	MHz
$MMCM\_F_{BANDWIDTH}$	Low MMCM bandwidth at typical(1)	1.00	1.00	1.00	1.00	MHz
	High MMCM bandwidth at typical(1)	4.00	4.00	4.00	4.00	MHz
$MMCM\_T_{STATPHAOFFSET}$	Static phase offset of the MMCM outputs(2)	0.12	0.12	0.12	0.12	ns
$MMCM\_T_{OUTJITTER}$	MMCM output jitter	Note 3				
$MMCM\_T_{OUTDUTY}$	MMCM output clock duty-cycle precision(4)	0.20	0.20	0.20	0.20	ns

Table 81: **Clock-Capable Clock Input Setup and Hold With PLL**

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1C/-1I/-1LI	-1Q	
Input Setup and Hold Time Relative to Clock-Capable Clock Input Signal for SSTL15 Standard.(1)							
$T_{PSPLLCC}$/ $T_{PHPLLCC}$	No delay clock-capable clock input and IFF(2) with PLL	XC7Z007S	N/A	3.03/–0.19	3.64/–0.19	N/A	ns
		XC7Z012S	N/A	3.15/–0.20	3.76/–0.20	N/A	ns
		XC7Z014S	N/A	3.17/–0.20	3.80/–0.20	N/A	ns
		XC7Z010	2.67/–0.19	3.03/–0.19	3.64/–0.19	N/A	ns
		XC7Z015	2.78/–0.20	3.15/–0.20	3.76/–0.20	N/A	ns
		XC7Z020	2.79/–0.20	3.17/–0.20	3.80/–0.20	N/A	ns
		XA7Z010	N/A	N/A	3.64/–0.19	3.64/–0.19	ns
		XA7Z020	N/A	N/A	3.80/–0.20	3.80/–0.20	ns
		XQ7Z020	N/A	3.17/–0.20	3.80/–0.20	3.80/–0.20	ns

Notes:

1. Setup and hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the global clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the global clock input signal using the fastest process, lowest temperature, and highest voltage.
2. IFF = Input flip-flop or latch
3. Use IBIS to determine any duty-cycle distortion incurred using various standards.

Table 82: **Data Input Setup and Hold Times Relative to a Forwarded Clock Input Pin Using BUFIO**

Symbol	Description	Speed Grade				Units
		-3	-2	-1C/-1I/-1LI	-1Q	
Input Setup and Hold Time Relative to a Forwarded Clock Input Pin Using BUFIO for SSTL15 Standard.						
T_{PSCS}/T_{PHCS}	Setup and hold of I/O clock	–0.38/1.39	–0.38/1.55	–0.38/1.86	–0.38/1.86	ns

Table 83: **Sample Window**

Symbol	Description	Speed Grade				Units
		-3	-2	-1C/-1I/-1LI	-1Q	
T_{SAMP}	Sampling error at receiver pins(1)	0.59	0.64	0.70	0.70	ns
T_{SAMP_BUFIO}	Sampling error at receiver pins using BUFIO(2)	0.35	0.40	0.46	0.46	ns

Notes:

1. This parameter indicates the total sampling error of the PL DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include:
   - CLK0 MMCM jitter
   - MMCM accuracy (phase offset)
   - MMCM phase shift resolution

   These measurements do not include package or clock tree skew.
2. This parameter indicates the total sampling error of the PL DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO clock network and IDELAY to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.

Table 92: **GTP Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTPTX}	Serial data rate range		0.500	–	F_{GTPMAX}	Gb/s
T_{RTX}	TX rise time	20%–80%	–	50	–	ps
T_{FTX}	TX fall time	80%–20%	–	50	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	500	ps
$V_{TXOOBVDPP}$	Electrical idle amplitude		–	–	20	mV
$T_{TXOOBTRANSITION}$	Electrical idle transition time		–	–	140	ns
$TJ_{6.25}$	Total Jitter(2)(3)	6.25 Gb/s	–	–	0.30	UI
$DJ_{6.25}$	Deterministic Jitter(2)(3)		–	–	0.15	UI
$TJ_{5.0}$	Total Jitter(2)(3)	5.0 Gb/s	–	–	0.30	UI
$DJ_{5.0}$	Deterministic Jitter(2)(3)		–	–	0.15	UI
$TJ_{4.25}$	Total Jitter(2)(3)	4.25 Gb/s	–	–	0.30	UI
$DJ_{4.25}$	Deterministic Jitter(2)(3)		–	–	0.15	UI
$TJ_{3.75}$	Total Jitter(2)(3)	3.75 Gb/s	–	–	0.30	UI
$DJ_{3.75}$	Deterministic Jitter(2)(3)		–	–	0.15	UI
$TJ_{3.2}$	Total Jitter(2)(3)	3.20 Gb/s(4)	–	–	0.2	UI
$DJ_{3.2}$	Deterministic Jitter(2)(3)		–	–	0.1	UI
$TJ_{3.2L}$	Total Jitter(2)(3)	3.20 Gb/s(5)	–	–	0.32	UI
$DJ_{3.2L}$	Deterministic Jitter(2)(3)		–	–	0.16	UI
$TJ_{2.5}$	Total Jitter(2)(3)	2.5 Gb/s(6)	–	–	0.20	UI
$DJ_{2.5}$	Deterministic Jitter(2)(3)		–	–	0.08	UI
$TJ_{1.25}$	Total Jitter(2)(3)	1.25 Gb/s(7)	–	–	0.15	UI
$DJ_{1.25}$	Deterministic Jitter(2)(3)		–	–	0.06	UI
TJ_{500}	Total Jitter(2)(3)	500 Mb/s	–	–	0.1	UI
DJ_{500}	Deterministic Jitter(2)(3)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TX phase alignment enabled for up to four consecutive transmitters (one fully populated GTP Quad).
2. Using PLL[0/1]_FBDIV = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. All jitter values are based on a bit-error ratio of $1e^{-12}$.
4. PLL frequency at 3.2 GHz and TXOUT_DIV = 2.
5. PLL frequency at 1.6 GHz and TXOUT_DIV = 1.
6. PLL frequency at 2.5 GHz and TXOUT_DIV = 2.
7. PLL frequency at 2.5 GHz and TXOUT_DIV = 4.

Date	Version	Description of Revisions
11/19/2014	1.14	Added V_{CCBRAM} to Introduction. Replaced -1L speed grade with -1LI and removed 1.0V row for V_{CCINT} and V_{CCBRAM} in Table 2. Updated the AC Switching Characteristics based upon Vivado 2014.4. Updated Vivado software version in Table 14. In Table 15, moved -1LI speed grade for XC7Z010, XC7Z015, and XC7Z020 devices from Advance to Production. In Table 16, added Vivado 2013.1 software version to -2E, -2I, -1C, and -1I speed grades of XC7Z010 and XC7Z020 devices, added Vivado 2014.4 software version to -1LI speed grade for all commercial devices, and removed table note. Added Selecting the Correct Speed Grade and Voltage in the Vivado Tools. Added Note 1 to Table 49. In Table 51, moved LPDDR2 row to end of 2:1 Memory Controllers section.
02/23/2015	1.15	Updated descriptions of V_{CCPINT} in Table 1 and Table 2. Added Note 6 to Table 11. In Table 13, changed maximum V_{ICM} value from 1.425V to 1.500V. Updated Table 22 title. Added Figure 1 and Table 23. In Table 34, updated minimum $T_{QSPIDCK2}$ and $T_{QSPICKD2}$ to 6 ns and 12.5 ns, respectively, and removed note 5. In Table 65, added $T_{RDCK\_DI\_ECCW}$/$T_{RCKD\_DI\_ECCW}$ and $T_{RDCK\_DI\_ECC\_FIFO}$/ $T_{RCKD\_DI\_ECC\_FIFO}$, updated T_{RCCK_EN}/T_{RCKC_EN} symbols, and updated Note 1. In Table 66, updated $T_{DSPDCK\_\{A, B\}\_MREG\_MULT}$/$T_{DSPCKD\_\{A, B\}\_MREG\_MULT}$ and $T_{DSPDCK\_\{A, D\}\_ADREG}$/ $T_{DSPCKD\_\{A, D\}\_ADREG}$ symbols, and replaced B input with A input for $T_{DSPDO\_A\_P}$. Removed minimum sample rate specification from Table 100.
09/22/2015	1.16	Updated data sheet per the customer notice XCN15034: *Zynq-7000 AP SoC Requirement for the PS Power-Off Sequence*. Assigned quiescent supply currents to -1LI speed grade XQ7Z020 device in Table 5. Updated PS Power-On/Off Power Supply Sequencing. Removed N/A from -1LI speed gradeXQ7Z020 device production software cell in Table 16. Added $F_{SMC\_REF\_CLK}$ to Table 33.
11/24/2015	1.17	Updated the AC Switching Characteristics based upon Vivado 2015.4. In Table 15, added -1LI speed grade to Production column for XQ7Z020. In Table 16, added Vivado 2015.4 software version to -1LI speed grade column for XQ7Z020. In Figure 4 and Figure 5, added extra clock pulse on QSPI_SCLK_OUT.
07/26/2016	1.18	Updated first sentence in PS Power-On/Off Power Supply Sequencing. Added T_{PSPOR} to Note 1 in Table 22. In Table 54, changed V_{MEAS} for LVCMOS (3.3V), LVTTL (3.3V), and PCI33 (3.3V) to 1.65V.
10/03/2016	1.19	Added XC7Z007S, XC7Z012S, and XC7Z014S throughout. Updated the AC Switching Characteristics based upon Vivado 2016.3.

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